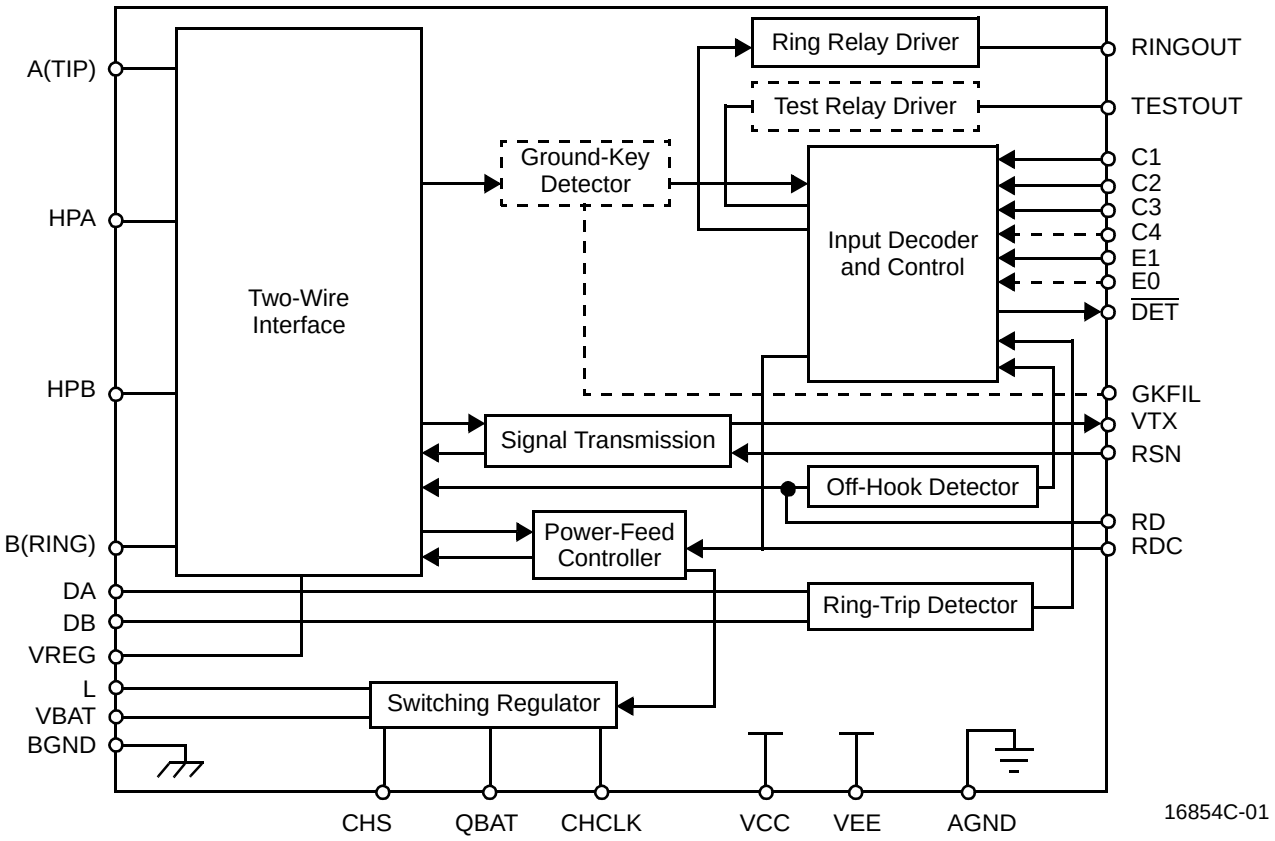
Am79534/Am79535

Subscriber Line Interface Circuit

DISTINCTIVE CHARACTERISTICS

- **Programmable constant-current feed**
- **Line-feed characteristics independent of battery variations**
- **Programmable loop-detect threshold**
- **On-chip switching regulator for low-power dissipation**
- **Pin for external ground-key noise-filter capacitor available**
- **Ground-key detect**
- **Two-wire impedance set by single external impedance**
- **Polarity reversal feature**
- **Tip Open state for ground-start lines**
- **Test relay driver optional**
- **On-hook transmission**

BLOCK DIAGRAM



Notes:

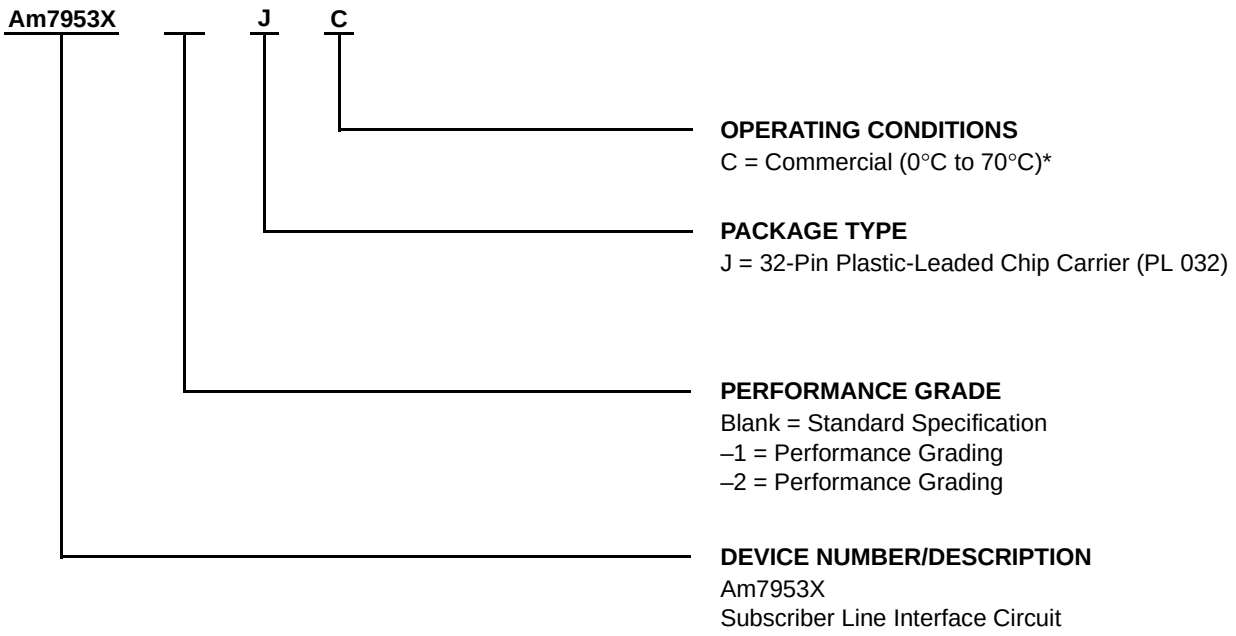
1. *Am79534—E0 and E1 inputs; ring and test relay drivers sourced internally to BGND.*
2. *Am79535—E0 and E1 inputs; ring relay driver sourced internally to BGND; ground-key filter pin.*
3. *Current gain (K_1) = 1000 for all parts.*

Publication# **16854** Rev: **D** Amendment: **/0**
Issue Date: **October 1999**

ORDERING INFORMATION

Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of the elements below.



Valid Combinations		
Am7953X	–1	DC
	–2	JC

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly released combinations, and to obtain additional data on AMD's standard military grade products.

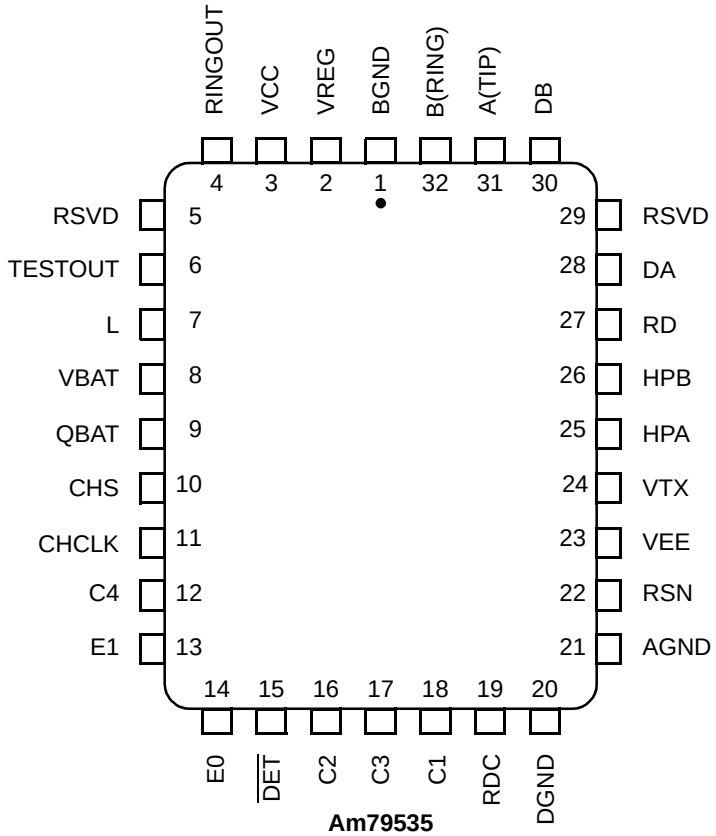
Note:

** Functionality of the device from 0°C to +70°C is guaranteed by production testing. Performance from –40°C to +85°C is guaranteed by characterization and periodic sampling of production units.*

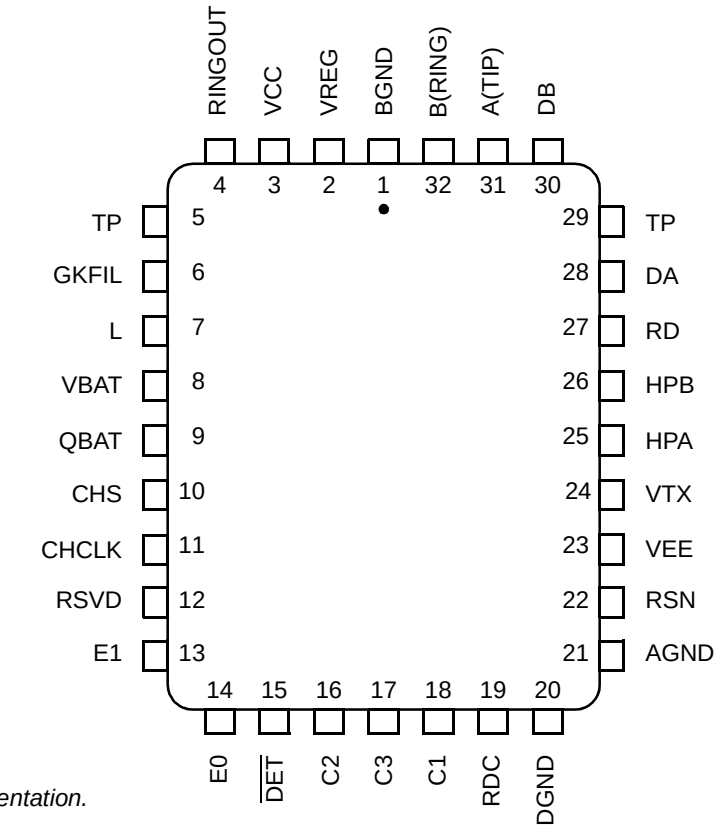
CONNECTION DIAGRAMS

Top View

Am79534



Am79535



Notes:

1. *Pin 1 is marked for orientation.*
2. *TP is a thermal conduction pin tied to substrate (QBAT).*
3. *RSVD = Reserved. Do not connect to these pins.*

PIN DESCRIPTIONS

Pin Names	Type	Description
AGND	Gnd	Analog (quiet) ground.
A(TIP)	Output	Output of A(TIP) power amplifier.
BGND	Gnd	Battery (power) ground.
B(RING)	Output	Output of B(RING) power amplifier.
C3–C1	Input	Decoder. TTL compatible. C3 is MSB and C1 is LSB.
C4	Input	Test relay driver command (Am79534). TTL compatible. A logic Low enables the driver.
CHCLK	Input	Chopper clock. Input to switching regulator (TTL compatible). Frequency = 256 kHz (nominal).
CHS	Input	Chopper stabilization. Connection for external stabilization components.
DA	Input	Ring-trip negative. Negative input to ring-trip comparator.
DB	Input	Ring-trip positive. Positive input to ring-trip comparator.
$\overline{\text{DET}}$	Output	Detector. A logic Low indicates that the selected detector is tripped. The detector is selected by the logic inputs (C3–C1, E0, and E1). The output is open-collector with a built-in 15 kΩ pull-up resistor.
DGND	Gnd	Digital ground.
E0	Input	Read enable. A logic High enables $\overline{\text{DET}}$. A logic Low disables $\overline{\text{DET}}$.
E1	Input	Ground-key enable. E1 = High connects the ground-key detector to $\overline{\text{DET}}$, and E1 = Low connects the off-hook or ring-trip detector to $\overline{\text{DET}}$.
GKFIL	Capacitor	Ground-key filter capacitor connection (Am79535). An external capacitor for filtering out high-frequency noise from the ground-key loop can be connected to this pin. An internal 36 kΩ, –20%, +40% resistor is provided to form an RC filter with the external capacitor. In versions that have a GKFIL pin, 3.3 nF minimum capacitance must be connected from the GKFIL pin to ground.
HPA	Capacitor	High-pass filter capacitor; A(TIP) side of high-pass filter capacitor.
HPB	Capacitor	High-pass filter capacitor; B(RING) side of high-pass filter capacitor.
L	Output	Switching regulator power transistor. Connection point for filter inductor and anode of catch diode. This pin has up to 60 V of pulse waveform on it and must be isolated from sensitive circuits. Keep the diode connections short because of the high currents and high di/dt.
QBAT	Battery	Quiet battery. Filtered battery supply for the signal processing circuits.
RD	Resistor	Detect resistor. Threshold modification and filter point for the off-hook detector.
RDC	Resistor	DC feed resistor. Connection point for the DC feed-current programming network which also connects to the Receiver Summing Node (RSN). V_{RDC} is negative for normal polarity and positive for reverse polarity.
RINGOUT	Output	Ring relay driver; sourcing from BGND with internal diode to QBAT.
RSN	Input	Receive summing node. The metallic current (AC and DC) between A(TIP) and B(RING) is equal to 1000 times the current into this pin. The networks that program receive gain, two-wire impedance, and feed current all connect to this node. This node is extremely sensitive. Route the 256 kHz chopper clock and switch lines away from the RSN node.
TESTOUT	Output	Test relay driver (Am79534); sourcing from BGND with internal diode to QBAT.
TP	Thermal	Thermal pin. Connection for heat dissipation. Internally connected to substrate (QBAT). Leave as open circuit or connected to QBAT. In both cases, the TP pins can connect to an area of copper on the board to enhance heat dissipation.
VBAT	Battery	Battery supply through an external protection diode.
VCC	Power	+5 V power supply.
VEE	Input	–5 V power supply.
VREG	Input	Regulated voltage. Provides negative power supply for power amplifiers and connection point for inductor, filter capacitor, and chopper stabilization.
VTX	Output	Transmit audio. This output is a unity gain version of the A(TIP) and B(RING) metallic voltage. VTX also sources the two-wire input impedance-programming network connects here.

ABSOLUTE MAXIMUM RATINGS

Storage temperature . . . . . –55°C to +150°C

V_{CC} with respect to AGND/DGND . . .–0.4 V to +7.0 V

V_{EE} with respect to AGND/DGND . . .+0.4 V to –7.0 V

V_{BAT} with respect to AGND/DGND . . +0.4 V to –70 V

Note: *Rise time of V_{BAT} (dv/dt) must be limited to 27 V/µs or less when Q_{BAT} bypass = 0.33 µF.*

BGND with respect to
AGND/DGND. . . . . .+1.0 V to –3.0 V

A(TIP) or B(RING) to BGND:

Continuous . . . . . –70 V to +1.0 V
10 ms (f = 0.1 Hz) . . . . . –70 V to +5.0 V
1 µs (f = 0.1 Hz). . . . . .–90 V to +10 V
250 ns (f = 0.1 Hz). . . . . .–120 V to +15 V

Current from A(TIP) or B(RING). . . . . ±150 mA

Voltage on RINGOUT . . . BGND to 70 V above Q_{BAT}

Voltage on TESTOUT . . . BGND to 70 V above Q_{BAT}

Current through relay drivers . . . . . 60 mA

Voltage on ring-trip inputs (DA and DB). . .V_{BAT} to 0 V

Current into ring-trip inputs . . . . . ±10 mA

Peak current into regulator switch (L pin) . . . 150 mA

Switcher transient peak off voltage on L pin . . +1.0 V

C4–C1, E1, CHCLK to
AGND/DGND. . . . . –0.4 V to (V_{CC} + 0.4 V)

Maximum power dissipation (see note) . . . T_A = 70°C
In 32-pin PLCC package . . . . . 1.74 W

Note: *Thermal limiting circuitry on chip will shut down the circuit at a junction temperature of about 165°C. The device should never be exposed to this temperature. Operation above 145°C junction temperature may degrade device reliability. See the SLIC Packaging Considerations for more information.*

Stresses above those listed under Absolute Maximum Ratings may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to Absolute Maximum Ratings for extended periods may affect device reliability.

OPERATING RANGES

Commercial (C) Devices

Ambient temperature . . . . . 0°C to +70°C*

V_{CC} . . . . . 4.75 V to 5.25 V

V_{EE} . . . . . –4.75 V to –5.25 V

V_{BAT} . . . . . –40 V to –58 V

AGND/DGND . . . . . 0 V

BGND with respect to
AGND/DGND . . . . . –100 mV to +100 mV

Load resistance on VTX to ground . . . . . 10 kΩ min

Operating Ranges define those limits between which the functionality of the device is guaranteed.

** Functionality of the device from 0°C to +70°C is guaranteed by production testing. Performance from –40°C to +85°C is guaranteed by characterization and periodic sampling of production units.*

ELECTRICAL CHARACTERISTICS

Description	Test Conditions (See Note 1)	Min	Typ	Max	Unit	Note
Analog (V_{TX}) output impedance			3		Ω	4
Analog (V_{TX}) output offset	0°C to +70°C	–35		+35	mV	
	–1*	–30		+30		
	–40°C to +85°C	–40		+40		4
	–1	–35		+35		4
Analog (RSN) input impedance	300 Hz to 3.4 kHz		1	20	Ω	4
Longitudinal impedance at A or B	300 Hz to 3.4 kHz			35	Ω	
Overload level Z_{2WIN} = 600 Ω to 900 Ω	4-wire 2-wire	–3.1		+3.1	Vpk	2
Transmission Performance, 2-Wire Impedance						
2-wire return loss (See Test Circuit D)	300 Hz to 500 Hz 500 Hz to 2.5 kHz 2.5 kHz to 3.4 kHz	26 26 20			dB	4, 10
Longitudinal Balance (2-Wire and 4-Wire, See Test Circuit C)						
R_L = 600 Ω Longitudinal to metallic L-T, L-4	300 Hz to 3.4 kHz	48			dB	
	–1*	52				
Longitudinal to metallic L-T, L-4	200 Hz to 1 kHz:					
	Normal polarity 0°C to +70°C –2*	63				
	Normal polarity –40°C to +85°C –2	58				4
	Reverse polarity –2	54				
	1 kHz to 3.4 kHz:					
	Normal polarity 0°C to +70°C –2*	58				
	Normal polarity –40°C to +85°C –2	54				4
	Reverse polarity –2	54				
Longitudinal signal generation 4-L	300 Hz to 800 Hz	40				
	300 Hz to 800 Hz –1*	42				
Longitudinal current capability per wire	Active state		25		mArms	4
	OHT state		18			
Insertion Loss (2- to 4-Wire and 4- to 2-Wire, See Test Circuits A and B)						
Gain accuracy	0 dBm, 1 kHz 0°C to +70°C	–0.15		+0.15	dB	
	0 dBm, 1 kHz –40°C to +85°C	–0.20		+0.20		4
	0 dBm, 1 kHz 0°C to +70°C –1*	–0.1		+0.1		
	0 dBm, 1 kHz –40°C to +85°C –1	–0.15		+0.15		4
Variation with frequency	300 Hz to 3.4 kHz (relative to 1 kHz):					
	0°C to +70°C	–0.1		+0.1		
	–40°C to +85°C	–0.15		+0.15		4
Gain tracking	+7 dBm to –55 dBm:					
	0°C to +70°C	–0.1		+0.1		
	–40°C to +85°C	–0.15		+0.15		4

Note:

** P.G. = Performance Grade (–2 performance parameters are equivalent to –1 performance parameters, except where indicated).*

ELECTRICAL CHARACTERISTICS (continued)

Description	Test Conditions (See Note 1)	Min	Typ	Max	Unit	Note
Balance Return Signal (4- to 4-Wire, See Test Circuit B)						
Gain accuracy	0 dBm, 1 kHz 0°C to +70°C 0 dBm, 1 kHz –40°C to +85°C 0 dBm, 1 kHz 0°C to +70°C –1* 0 dBm, 1 kHz –40°C to +85°C –1	 –0.15 –0.20 –0.1 –0.15		 +0.15 +0.20 +0.1 +0.15	dB	 4 4
Variation with frequency	300 Hz to 3.4 kHz (relative to 1 kHz): 0°C to +70°C –40°C to +85°C					
		  –0.1 –0.15		 +0.1 +0.15		 4
Gain tracking	+7 dBm to –55 dBm: 0°C to +70°C –40°C to +85°C	 –0.1 –0.15		 +0.1 +0.15		 4 4
Group delay	f = 1 kHz		5.3		µs	4
Total Harmonic Distortion (2- to 4-Wire or 4- to 2-Wire, See Test Circuits A and B)						
Total harmonic distortion	0 dBm, 300 Hz to 3.4 kHz +9 dBm, 300 Hz to 3.4 kHz		–64 –55	–50 –40	dB	
Idle Channel Noise						
C-message weighted noise	2-wire: 0°C to +70°C 2-wire: 0°C to +70°C –1* 2-wire: –40°C to +85°C		+7 +7 +7	+15 +12 +15	dBrnC	 4
	4-wire 0°C to +70°C 4-wire 0°C to +70°C –1* 4-wire –40°C to +85°C		+7 +7 +7	+15 +12 +15		 4
Psophometric weighted noise	2-wire 0°C to +70°C 2-wire 0°C to +70°C –1* 2-wire –40°C to +85°C		–83 –83 –83	–75 –78 –75	dBmp	7 4
	4-wire 0°C to +70°C 4-wire 0°C to +70°C –1* 4-wire –40°C to +85°C		–83 –83 –83	–75 –78 –75		7 4
Single Frequency Out-of-Band Noise (See Test Circuit E)						
Metallic	4 kHz to 9 kHz 9 kHz to 1 MHz 256 kHz and harmonics		–76 –76 –57		dBm	4, 5, 9 4, 5, 9 4, 5
Longitudinal	1 kHz to 15 kHz Above 15 kHz 256 kHz and harmonics		–70 –85 –57			4 4, 5, 9 4, 5
DC Feed Currents (See Figure 1) BAT = –48 V						
Active state loop-current accuracy	I_{LOOP} (nominal) = 40 mA	–7.5		+7.5	%	
OHT state	R_L = 600 Ω	18	20	22	mA	
Tip Open state	R_L = 600 Ω			1.0		
Open Circuit state	R_L = 0 Ω			1.0		
Fault current limit, I_LLIM (I_{AX} + I_{BX})	A and B shorted to GND			130		

ELECTRICAL CHARACTERISTICS (continued)

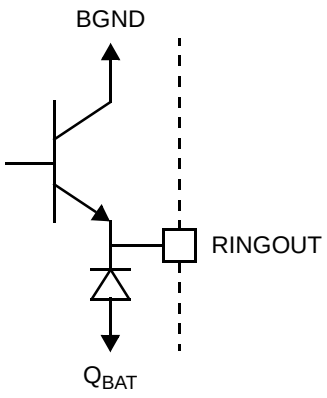
Description	Test Conditions (See Note 1)	Min	Typ	Max	Unit	Note
Power Dissipation BAT = –48 V, Normal Polarity						
On-hook Open Circuit state	 –1*		35 35	120 80	mW	
On-hook OHT state	 –1*		135 135	250 200		
On-hook Active state	 –1*		200 200	400 300		
Off-hook OHT state	R_L = 600 Ω		500	750		
Off-hook Active state	R_L = 600 Ω		650	1000		
Supply Currents						
V_{CC} on-hook supply current	Open Circuit state OHT state Active state		3.0 6.0 7.5	4.5 10.0 12.0	mA	
V_{EE} on-hook supply current	Open Circuit state OHT state Active state		1.0 2.2 2.7	2.3 3.5 6.0		
V_{BAT} on-hook supply current	Open Circuit state OHT state Active state		0.4 3.0 4.0	1.0 5.0 6.0		
Power Supply Rejection Ratio (V_{RIPPLE} = 50 mVrms)						
V_{CC}	50 Hz to 3.4 kHz –1*	25 30	45 45		dB	6, 7
	3.4 kHz to 50 kHz –1	22 25	35 35			
V_{EE}	50 Hz to 3.4 kHz –1*	20 25	40 40			
	3.4 kHz to 50 kHz –1	10 10	25 25			
V_{BAT}	50 Hz to 3.4 kHz –1*	27 30	45 45			
	3.4 kHz to 50 kHz –1	20 25	40 40			
Off-Hook Detector						
Current threshold accuracy	I_{DET} = 365/R_D nominal	–20		+20	%	
Ground-Key Detector Thresholds, Active State, BAT = –48 V (See Test Circuit F)						
Ground-key resistance threshold	B(RING) to GND	2.0	5.0	10.0	kΩ	
Ground-key current threshold	B(RING) to GND Midpoint to GND		9		mA	8
Ring-Trip Detector Input						
Bias current		–5	–0.05		µA	
Offset voltage	Source resistance 0 to 2 MΩ	–50	0	+50	mV	11

ELECTRICAL CHARACTERISTICS (continued)

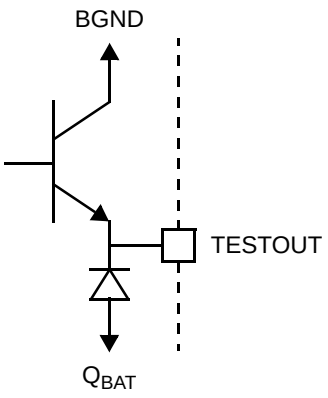
Description	Test Conditions (See Note 1)	Min	Typ	Max	Unit	Note
Logic Inputs (C4–C1, E0, E1, and CHCLK)						
Input High voltage		2.0			V	
Input Low voltage				0.8		
Input High current	All inputs except E1 Input E1	–75 –75		40 45	µA	
Input Low current		–0.4			mA	
Logic Output ($\overline{DET}$)						
Output Low voltage	I_{OUT} = 0.8 mA			0.4	V	
Output High voltage	I_{OUT} = –0.1 mA	2.4				
Relay Driver Outputs (RINGOUT, TESTOUT)						
On voltage	50 mA source	BGND – 2	BGND – 0.95		V	
Off leakage			0.5	100	µA	
Clamp voltage	50 mA sink	Q_{BAT} – 2			V	

RELAY DRIVER SCHEMATICS

Am79534/Am79535



Am79534



16854C-03

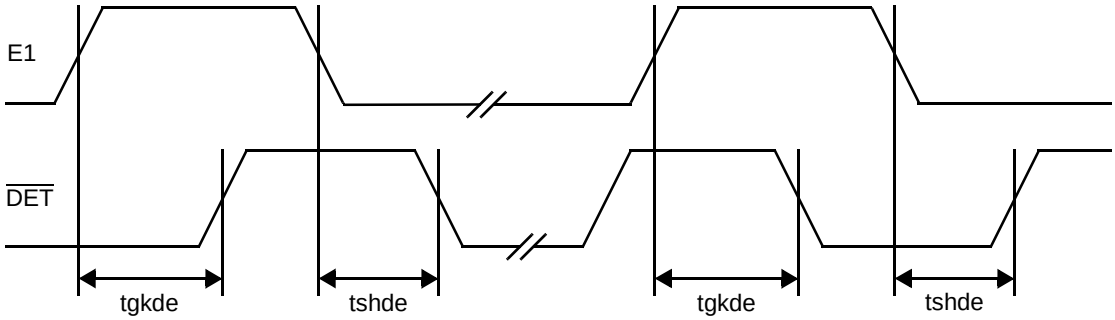
SWITCHING CHARACTERISTICS

Am79534/Am79535

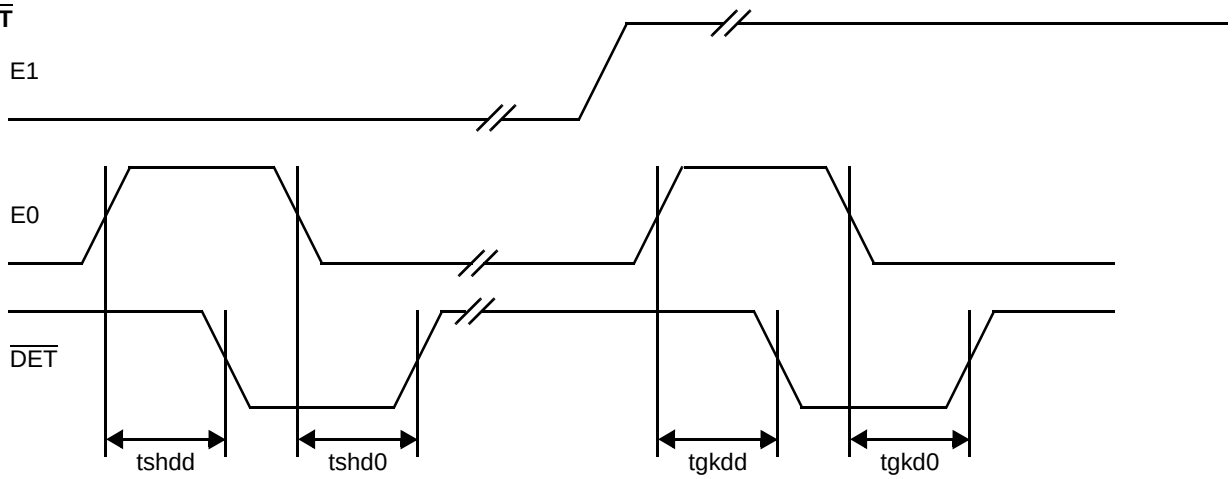
Symbol	Parameter	Test Conditions	Temperature Range	Min	Typ	Max	Unit	Note
tgkde	E1 Low to $\overline{\text{DET}}$ High (E0 = 1)	Ground-key Detect state R_L open, R_G connected (See Figure H)	0°C to +70°C –40°C to +85°C			3.8 4.0	µs	4
	E1 Low to $\overline{\text{DET}}$ Low (E0 = 1)		0°C to +70°C –40°C to +85°C			1.1 1.6		
tgkdd	E0 High to $\overline{\text{DET}}$ Low (E1 = 0)		0°C to +70°C –40°C to +85°C			1.1 1.6		
tgkd0	E0 Low to $\overline{\text{DET}}$ High (E1 = 0)		0°C to +70°C –40°C to +85°C			3.8 4.0		
tshde	E1 High to $\overline{\text{DET}}$ Low (E0 = 1)	Switchhook Detect state R_L = 600 Ω, R_G open (See Figure G)	0°C to +70°C –40°C to +85°C			1.2 1.7		
	E1 High to $\overline{\text{DET}}$ High (E0 = 1)		0°C to +70°C –40°C to +85°C			3.8 4.0		
tshdd	E0 High to $\overline{\text{DET}}$ Low (E1 = 1)		0°C to +70°C –40°C to +85°C			1.1 1.6		
tshd0	E0 Low to $\overline{\text{DET}}$ High (E1 = 1)		0°C to +70°C –40°C to +85°C			3.8 4.0		

SWITCHING WAVEFORMS
Am79534/Am79535

E1 to $\overline{\text{DET}}$



E0 to $\overline{\text{DET}}$

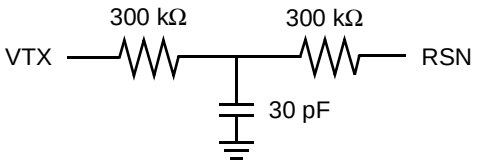


Note:
All delays measured at 1.4 V level.

16854C-02

Notes:

1. *Unless otherwise noted, test conditions are BAT = –48 V, V_{CC} = +5 V, V_{EE} = –5 V, R_L = 600 Ω, C_{HP} = 0.22 μF, $R_{DC1} = R_{DC2}$ = 31.25 kΩ, C_{DC} = 0.1 μF, R_D = 51.1 kΩ, no fuse resistors, two-wire AC output impedance, programming impedance (Z_T) = 600 kΩ resistive, receive input summing impedance (Z_{RX}) = 300 kΩ resistive. (See Table 2 for component formulas.)*
2. *Overload level is defined when THD = 1%.*
3. *Balance return signal is the signal generated at V_{TX} by V_{RX}. This specification assumes the two-wire AC load impedance matches the impedance programmed by Z_T.*
4. *Not tested in production. This parameter is guaranteed by characterization or correlation to other tests.*
5. *These tests are performed with a longitudinal impedance of 90 Ω and metallic impedance of 300 Ω for frequencies below 12 kHz and 135 Ω for frequencies greater than 12 kHz. These tests are extremely sensitive to circuit board layout.*
6. *This parameter is tested at 1 kHz in production. Performance at other frequencies is guaranteed by characterization.*
7. *When the SLIC is in the Anti-sat 2 operating region, this parameter is degraded. The exact degradation depends on system design. The Anti-sat 2 region occurs at high loop resistances when $|V_{BAT}| - |V_{AX} - V_{BX}|$ is less than approximately 11 V.*
8. *"Midpoint" is defined as the connection point between two 300 Ω series resistors connected between A(TIP) and B(RING).*
9. *Fundamental and harmonics from 256 kHz switch-regulator chopper are not included.*
10. *Assumes the following Z_T network:*



11. Tested with 0 Ω source impedance. 2 MΩ is specified for system design purposes only.

12. Group delay can be reduced considerably by using a Z_T network such as that shown in Note 10 above. The network reduces the group delay to less than 2 μs. The effect of group delay on linecard performance may be compensated for by using QSLAC™ or DSLAC™ devices.

Table 1. SLIC Decoding

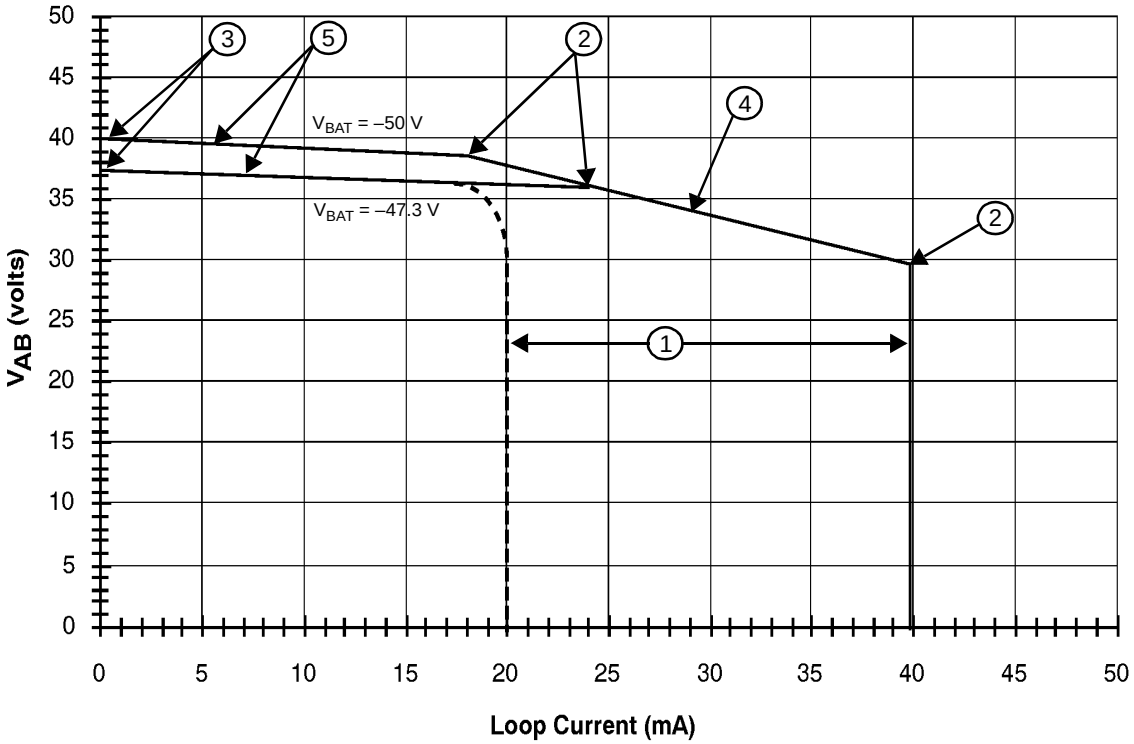
					$\overline{\text{DET}}$ Output (E0 = 1*)	
State	**C3**	**C2**	**C1**	**Two-Wire Status**	**E1 = 0**	**E1 = 1**
0	0	0	1	Open Circuit	Ring trip	Ring trip
1	0	0	1	Ringing	Ring trip	Ring trip
2	0	1	0	Active	Loop detector	Ground key
3	0	1	1	On-hook TX (OHT)	Loop detector	Ground key
4	1	0	0	Tip Open	Loop detector	—
5	1	0	1	Reserved	Loop detector	—
6	1	1	0	Active Polarity Reversal	Loop detector	Ground key
7	1	1	1	OHT Polarity Reversal	Loop detector	Ground key

Note:
** For the Am79534 and Am79535, a logic Low on E0 disables the $\overline{DET}$ output into the open-collector state.*

Table 2. User-Programmable Components

$Z_T = 1000(Z_{2WIN} - 2R_F)$	Where Z_T is connected between the VTX and RSN pins. The fuse resistors are R_F, and Z_{2WIN} is the desired 2-wire AC input impedance. When computing Z_T, the internal current amplifier pole and any external stray capacitance between VTX and RSN must be taken into account.
$Z_{RX} = \frac{Z_L}{G_{42L}} \bullet \frac{1000 \bullet Z_T}{Z_T + 1000(Z_L + 2R_F)}$	Where Z_{RX} is connected from V_{RX} to the RSN pin, Z_T is defined above, and G_{42L} is the desired receive gain.
$R_{DC1} + R_{DC2} = \frac{2500}{I_{FEED}}$ $C_{DC} = 1.5\ ms \bullet \frac{R_{DC1} + R_{DC2}}{R_{DC1} \bullet R_{DC2}}$	Where R_{DC1}, R_{DC2}, and C_{DC} form the network connected to the RDC pin. R_{DC1} and R_{DC2} are approximately equal.
$R_D = \frac{365}{I_T}, \quad C_D = \frac{0.5\ ms}{R_D}$	Where R_D and C_D form the network connected from RD to –5 V and I_T is the threshold current between on hook and off hook.

DC FEED CHARACTERISTICS



Notes:

1. *Constant-current region:*

   Active state: $I_L = \frac{2500}{R_{DC}}$

   OHT state: $I_L = \frac{1}{2} \bullet \frac{2500}{R_{DC}}$

2. *Anti-sat turn-on (Active state):*

   Anti-sat –1: $V_{AB} = 29.95\ V$

   Anti-sat –2: $V_{AB} = 1.082|V_{BAT}| - 15.149$

3. *Open Circuit voltage (Active state):*

   $V_{AB} = 0.9|V_{BAT}| - 4.995, \quad |V_{BAT}| < 56.9\ V$

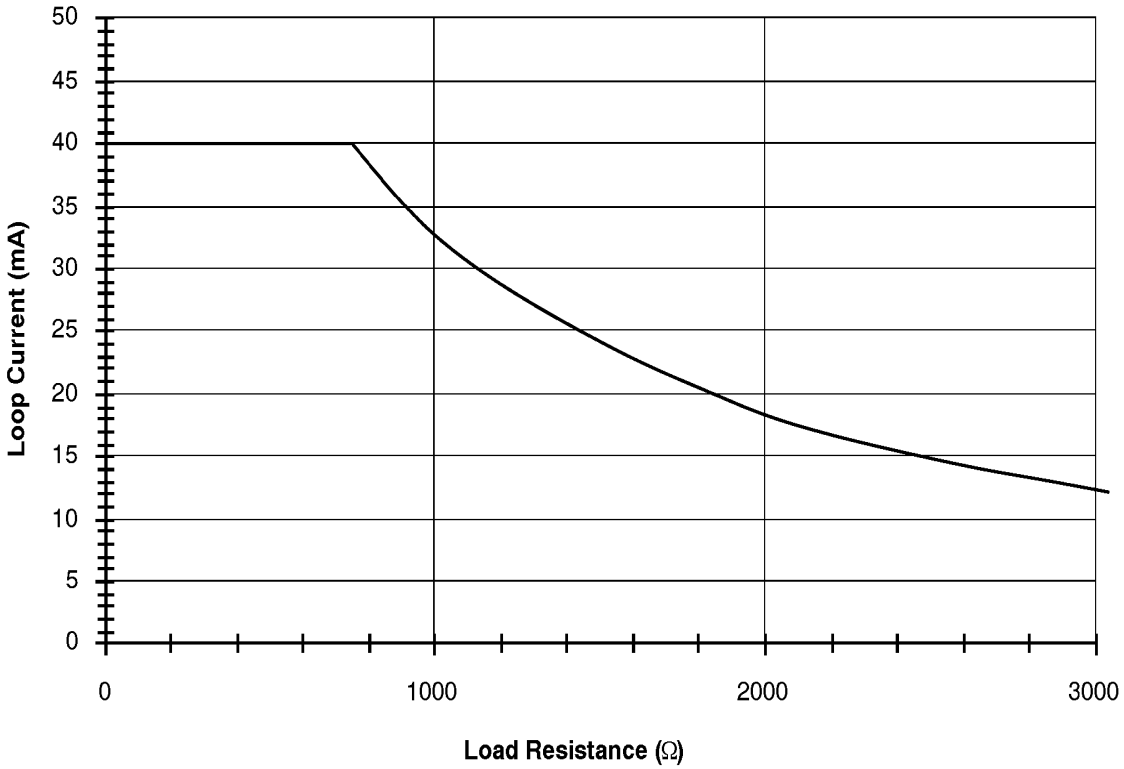
   $V_{AB} = 46.25\ V, \quad |V_{BAT}| \geq 56.9\ V$

4. *Anti-sat –1 region:* $V_{AB} = 46.25 - I_L \frac{R_{DC}}{150.6}$

5. *Anti-sat –2 region:* $V_{AB} = 0.9|V_{BAT}| - 4.995 - I_L \frac{R_{DC}}{1128}$

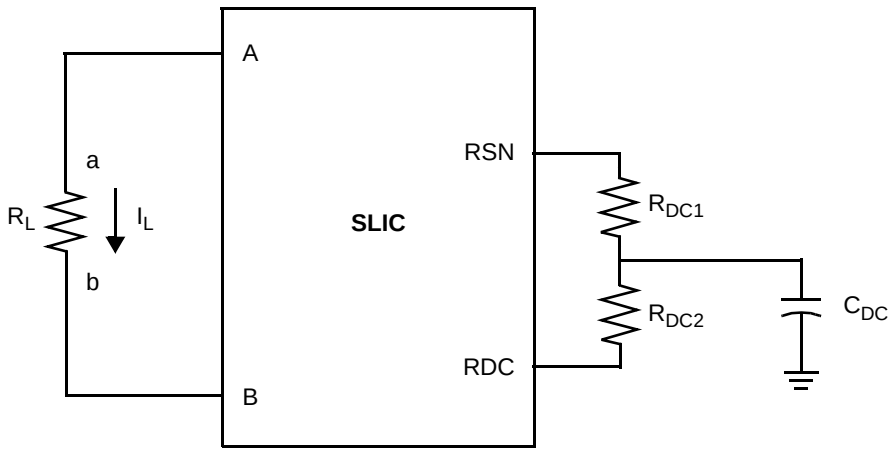
a. V_A–V_B (V_{AB}) Voltage vs. Loop Current (Typical)

DC FEED CHARACTERISTICS (continued)



R_{DC} = 62.5 kΩ
V_{BAT} = –47.3 V

b. Loop Current vs. Load Resistance (Typical)

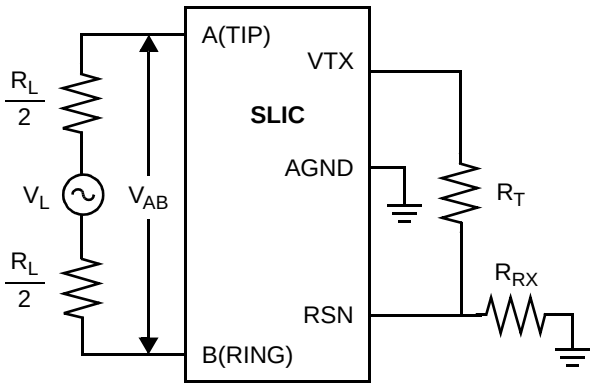


Feed current programmed by R_{DC1} and R_{DC2}

c. Feed Programming

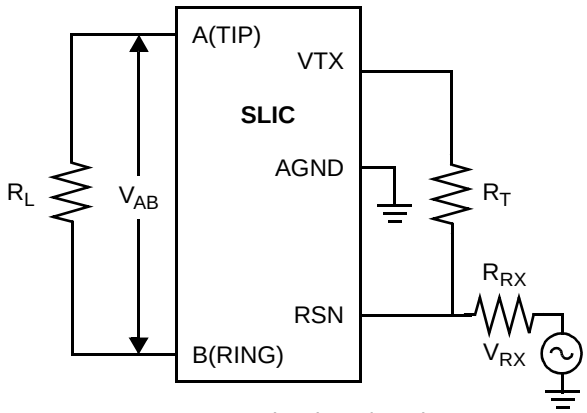
Figure 1. DC Feed Characteristics

TEST CIRCUITS



$I_{L2\text{-}4} = -20 \log (V_{TX} / V_{AB})$

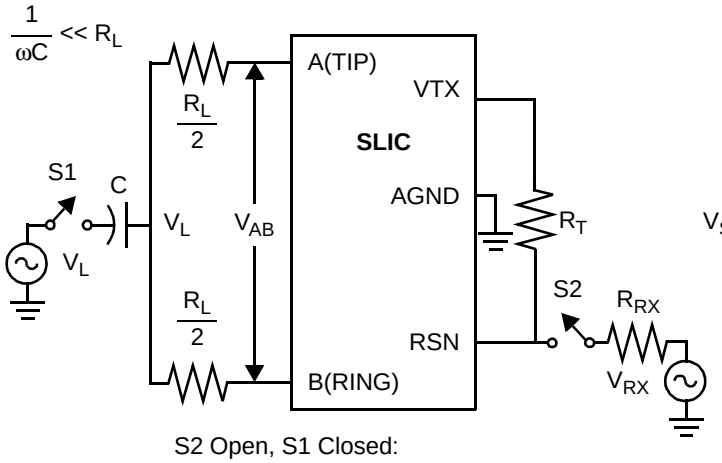
A. Two- to Four-Wire Insertion Loss



$I_{L4\text{-}2} = -20 \log (V_{AB} / V_{RX})$

$BRS = 20 \log (V_{TX} / V_{RX})$

B. Four- to Two-Wire Insertion Loss and Balance Return Signal



S2 Open, S1 Closed:

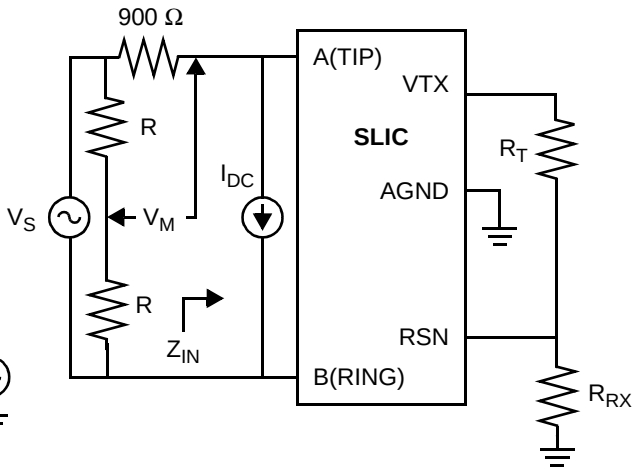
L-T Long. Bal. = $20 \log (V_{AB} / V_L)$

L-4 Long. Bal. = $20 \log (V_{TX} / V_L)$

S2 Closed, S1 Open:

4-L Long. Sig. Gen. = $20 \log (V_L / V_{RX})$

C. Longitudinal Balance



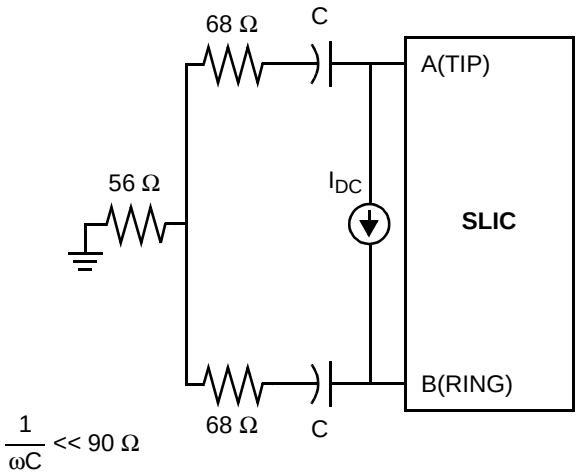
Note:

Z_D is the desired impedance (e.g., the characteristic impedance of the line).

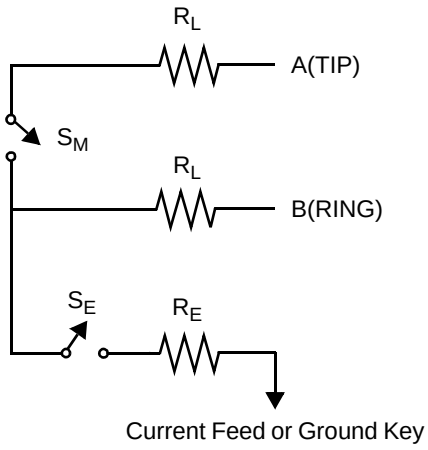
$R_L = -20 \log (2 V_M / V_S)$

D. Two-Wire Return Loss Test Circuit

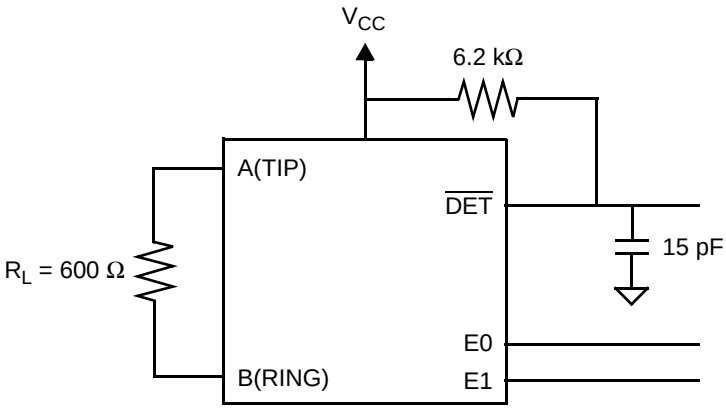
TEST CIRCUITS (continued)



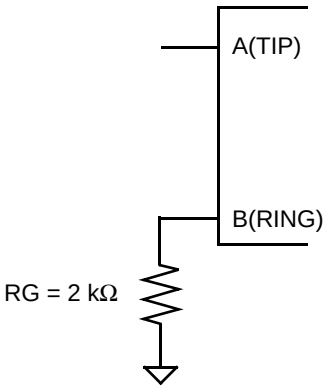
E. Single-Frequency Noise



F. Ground-Key Detection



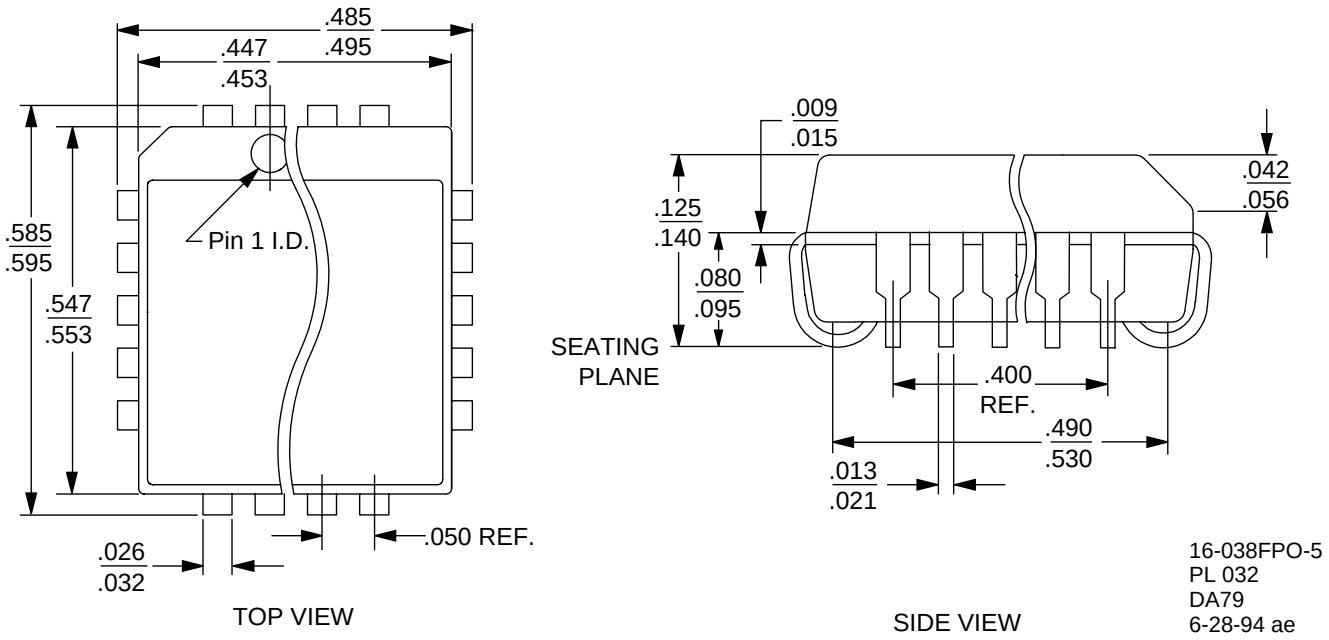
G. Loop-Detector Switching



H. Ground-Key Switching

PHYSICAL DIMENSION

PL032



REVISION SUMMARY

Revision B to Revision C

- Minor changes to the data sheet style and format were made to conform to AMD standards.
- Connection Diagrams—Changed pin 29 from TP to RSVD in the Am79534 diagram.

Revision C to Revision D

- In Table 1, SLIC Decoding, the Open Circuit state of 001 was changed to 000.
- In Pin Description table, inserted/changed TP pin description to: “Thermal pin. Connection for heat dissipation. Internally connected to substrate (QBAT). Leave as open circuit or connected to QBAT. In both cases, the TP pins can connect to an area of copper on the board to enhance heat dissipation.”
- Minor changes to the data sheet style and format were made to conform to AMD standards.

Revision D to Revision E

- The physical dimension (PL032) was added to the Physical Dimension section.
- Deleted the Ceramic DIP and Plastic DIP parts (Am79530 and Am79531) and references to them.
- Updated Pin Desciption to correct inconsistencies.

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